

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re Patent Application of

KOCHERGIN et al.

Atty. Ref.: 340-80

Serial No. 10/686,520

TC/A.U.: 2872

Filed: 16 October 2003

Examiner:

For: SPECTRAL FILTER FOR GREEN AND LONGER WAVELENGTHS

May 28, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

## INFORMATION DISCLOSURE STATEMENT

In accordance with Rule 97, the undersigned attorney submits the documents listed on the attached form PTO-1449. A copy of each non-U.S. patent document is enclosed.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy to the undersigned as an indication that the attached documents have been considered and made of record in this case.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: \_\_\_\_\_

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CITATION TO			10/686,520					
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Date Considered

\*Examiner

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